FORM PTO-1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	ATTORNEY DOCKET NO.: ASC-049C1 APPLICANT(S): Fitzgerald SERIAL NO.: 10/774,890 FILING DATE: February 9, 2004 GROUP: 2818

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

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